



FQU20N06L

N-Channel QFET[®] MOSFET

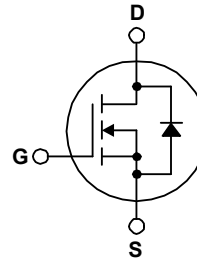
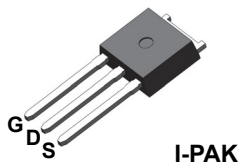
60 V, 17.2 A, 42 mΩ

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 17.2 A, 60 V, $R_{DS(on)} = 42 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 8.6 \text{ A}$
- Low Gate Charge (Typ. 9.5 nC)
- Low Crss (Typ. 35 pF)
- 100% Avalanche Tested
- Low Level Gate Drive Requirements Allowing Direct Operation Form Logic Drivers



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQU20N06LTU	Unit
V_{DSS}	Drain-Source Voltage	60	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	17.2	A
		10.9	A
I_{DM}	Drain Current - Pulsed (Note 1)	68.8	A
V_{GSS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	170	mJ
I_{AR}	Avalanche Current (Note 1)	17.2	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	3.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	7.0	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	2.5	W
	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	38	W
		0.30	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQU20N06LTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.28	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQU20N06LTU	FQU20N06L	IPAK	Tube	N/A	N/A	70 units

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
--------	-----------	-----------------	------	------	------	------

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.06	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 48\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.0	--	2.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 8.6\text{ A}$	--	0.046	0.06	Ω
		$V_{GS} = 5\text{ V}, I_D = 8.6\text{ A}$	--	0.057	0.075	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 25\text{ V}, I_D = 8.6\text{ A}$	--	11	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	480	630	pF
C_{oss}	Output Capacitance		--	175	230	pF
C_{rss}	Reverse Transfer Capacitance		--	35	45	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30\text{ V}, I_D = 10.5\text{ A},$ $R_G = 25\ \Omega$	--	10	30	ns
t_r	Turn-On Rise Time		--	165	340	ns
$t_{d(off)}$	Turn-Off Delay Time		--	35	80	ns
t_f	Turn-Off Fall Time		(Note 4)	--	70	150
Q_g	Total Gate Charge	$V_{DS} = 48\text{ V}, I_D = 21\text{ A},$ $V_{GS} = 5\text{ V}$	--	9.5	13	nC
Q_{gs}	Gate-Source Charge		--	2.5	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4)	--	5.5	--

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	17.2	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	68.8	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 17.2\text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_F = 21\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	54	--	ns
Q_{rr}	Reverse Recovery Charge		--	75	--	nC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. $L = 670\ \mu\text{H}$, $I_{AS} = 17.2\text{ A}$, $V_{DD} = 25\text{ V}$, $R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 21\text{ A}$, $di/dt \leq 300\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.